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A journal devoted to the properties of interfaces
in relation to the synthesis and behaviour of materials



North-Holland

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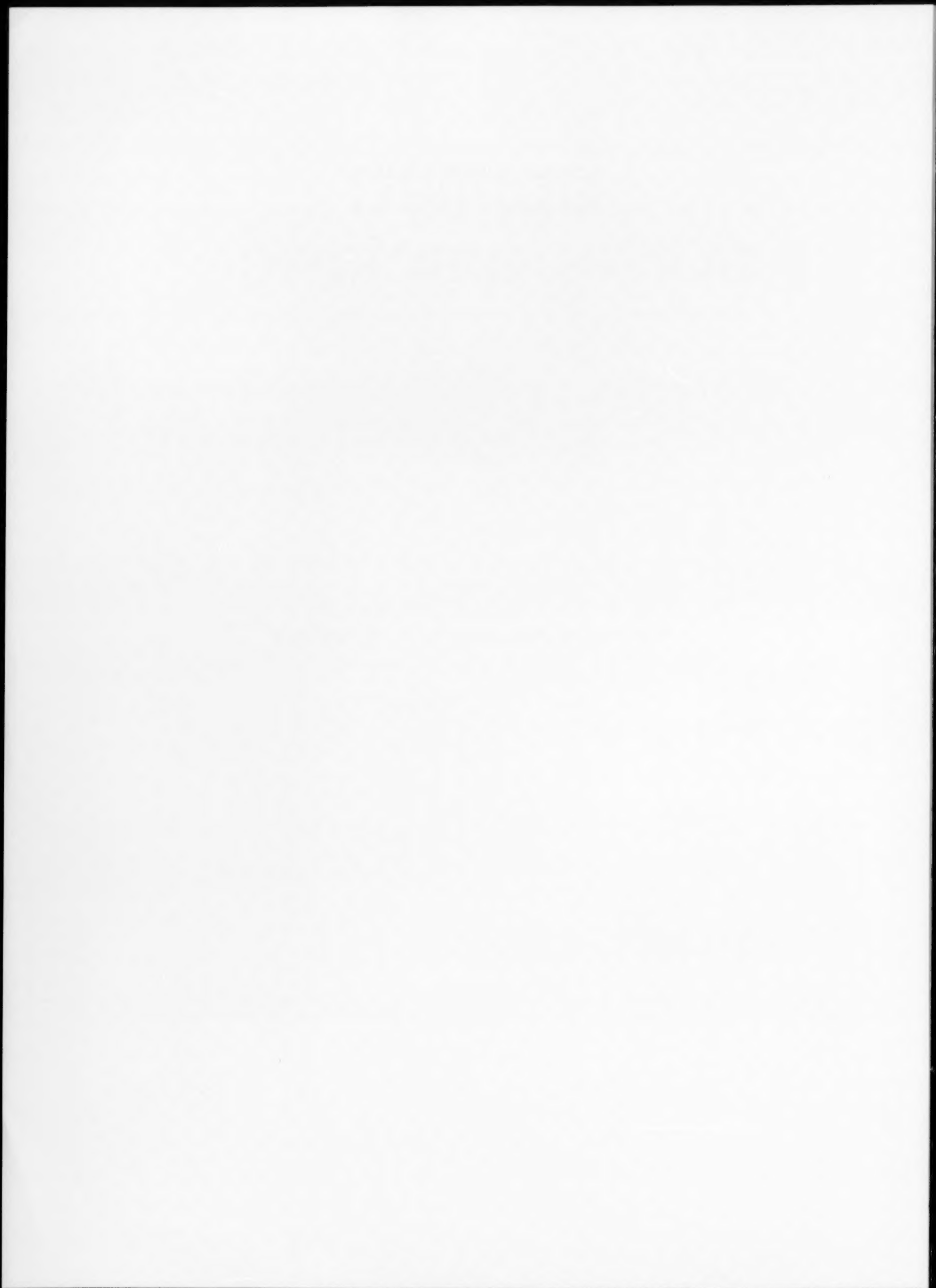
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A JOURNAL DEVOTED TO THE PROPERTIES OF INTERFACES
IN RELATION TO THE SYNTHESIS AND BEHAVIOUR OF MATERIALS

Editors:

L.C. Feldman, Murray Hill, NJ, USA
W.F. van der Weg, Utrecht, The Netherlands

Master Index to Volumes 31-40



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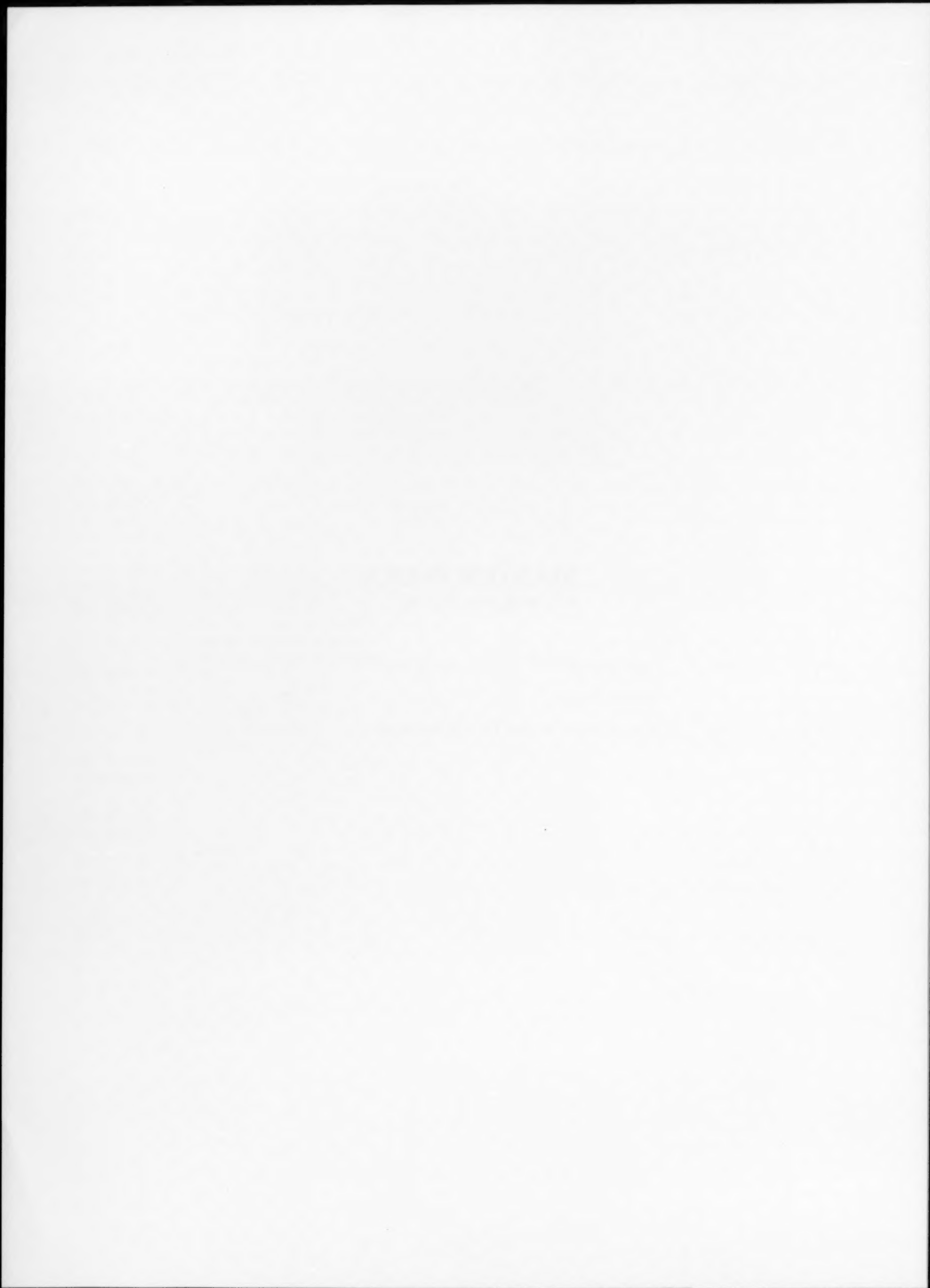
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- [1] C. Nöbl, C. Benndorf and T.E. Madey, *Surf. Sci.* 157 (1985) 29.
- [2] D.R. Baer and M.T. Thomas, *Appl. Surf. Sci.* 26 (1986) 150.
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| | |
|---|---|
| I (cap.), l (el), 1 (one), ' (prime) | c, C; k, K, κ (kappa); p, P, ρ (rho) |
| o (lower case), O (cap.), 0 (zero), ° (deg) | u, v (lower case), ν (nu), V (cap.) |
| \times (times), x (lower case), X (cap.) | Σ (sigma), Σ (sum); Π (pi), Π (product); etc. |

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